

Prof. Levan Chkhartishvili is a native of Tbilisi (Georgia) and has been on faculty on the Department of Engineering Physics at the Georgian Technical University (GTU) since 1992. As a professor at GTU, he collaborates with the F. Tavadze Institute of Metallurgy and Materials Science (FTIMMS). He also collaborated with Scientific-Industrial Association 'Mion', Ilia State University (ISU), Liquid Light Inc. Labs, and other institutions.

He completed his MSc in Theoretical Physics (1980) and obtained his scientific degrees of Candidate (1989) and Doctor (2006) of Sciences in Solid State Physics at the I. Javakhishvili Tbilisi State University (TSU).

Having been involved in materials research for about 35 years, Prof. Levan Chkhartishvili has developed his expertise in the fields of geometrical and electronic structures of dielectrics and semiconductors (boron, germanium, silicon, gallium arsenide, boron nitride), transport phenomena in solids, isotopic effects, materials for shielding from ionizing irradiations, physics of nanosystems. He has (co)authored about 250 publications, among them 2 monographs and about 80 book chapters / papers in referred journals.

He is Editor & Publisher of *Nano Studies*, and Editorial / Advisory Board Member of *American Journal of Materials Science*, *European Chemical Bulletin*, and *Karbala Journal of Modern Sciences*, and (Co)editor of several collections of scientific papers.

Prof. Levan Chkhartishvili is a Member of Georgian Physical Society (GPS), Euroscience (ES), and American Chemical Society (ACS). He served as a Member of Organizing / Scientific Committees of several conferences. In particular, he is a Standing Member of the International Scientific Committee of the International Symposia on Boron, Borides and Related Materials (ISBBs).